## What is claimed is:

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1. A semiconductor light emitting element of a monolithic structure, comprising:

a first-conductivity-type semiconductor substrate;

an active layer formed on the first-conductivity-type semiconductor substrate;

a second-conductivity-type clad layer formed on the active layer; and

a current diffusion layer formed on the second-conductivity-type clad layer,

wherein the active layer is of a first conductivity type.

- 2. The element of claim 1, wherein the semiconductor substrate is a GaAs substrate, and the active layer is a semiconductor layer containing Al, Ga, As, In and/or P as constituent atoms.
- 3. The element of claim 1, wherein the active layer contains Si or Se atoms as first-conductivity-type impurities.
- The element of claim 1, wherein the active layer contains Zn or Mg as first-conductivity-type impurities.
- 20 5. The element of claim 1, wherein the active layer contains first-conductivity-type impurities in a concentration between  $3\times10^{16}$  and  $10\times10^{16}$  cm<sup>-3</sup>.
  - 6. The element of claim 1, wherein a spacer layer is provided between the active layer and the
- 25 second-conductivity-type clad layer.

- 7. The element of claim 6, wherein the spacer layer is either a non-doped layer or a second-conductivity-type layer.
- 8. The element of claim 6, wherein the spacer layer has a thickness of 0.1 to 0.2  $\mu$  m.
- 5 9. The element of claim 6, wherein the spacer layer is formed of the same constituent atoms in the same composition as is the case of the second-conductivity-type clad layer.
  - 10. The element of claim 1 or 9, wherein the active layer is formed of GaAlInP, the second-conductivity-type clad layer is
- also formed of GaAlInP, and the Al mixed crystal ratio of the active layer is lower than that of the second-conductivity-type clad layer.
  - 11. The element of claim 10, wherein the Al mixed crystal ratios of the second-conductivity-type clad layer and the
- spacer layer are approximately 0.7, and that of the active layer is approximately 0.3.